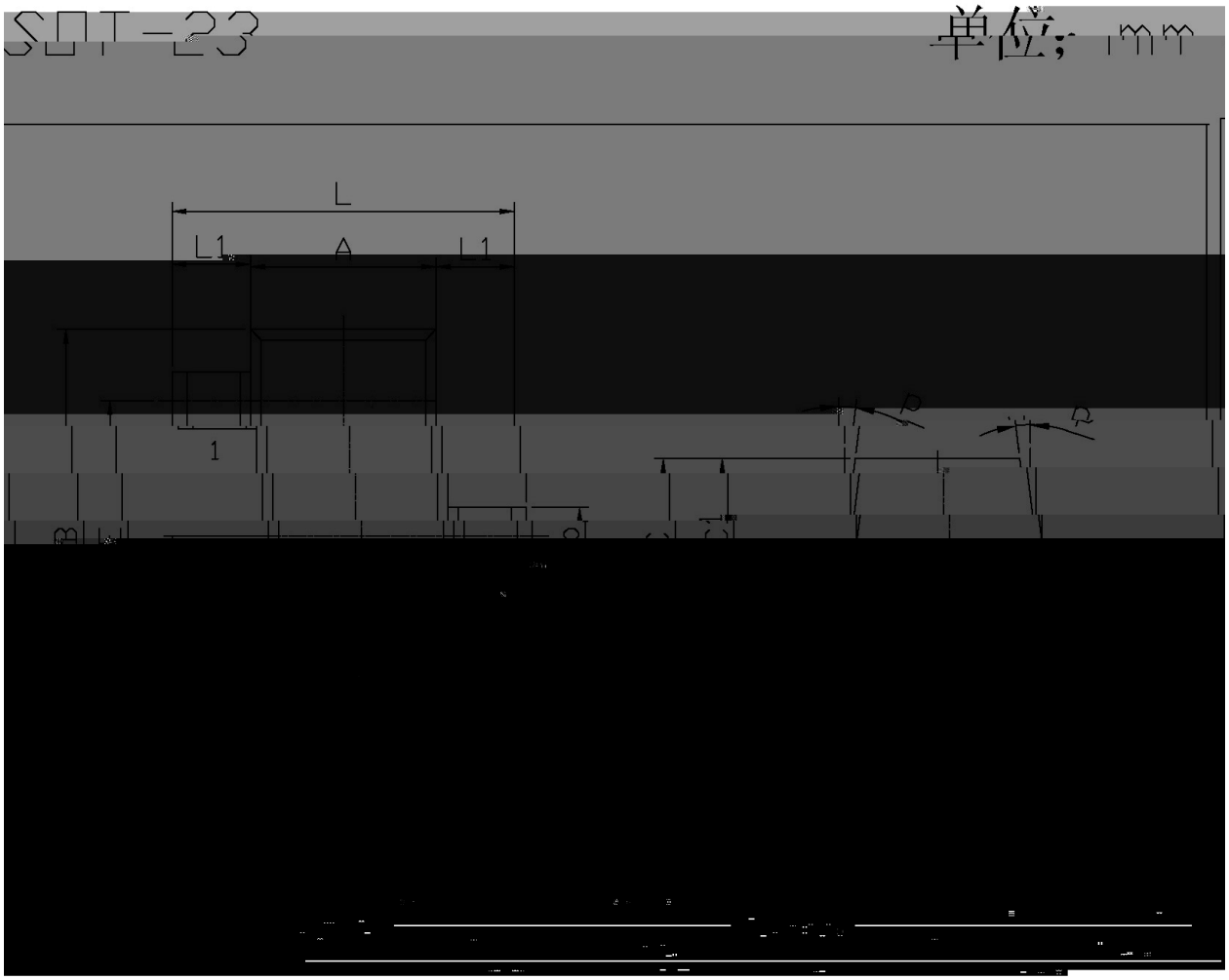
VRW056 ṂṂ Ḷ SQS ÆṀ ч s ‖ ㄱ Silicon PNP transistor in a SOT-23 Plastic Package.

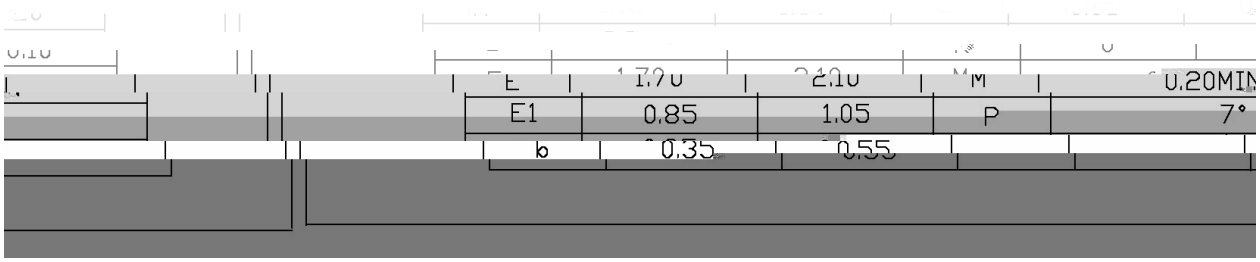
ㅊ ɔ ㅣㅣ ш ` ı Ӈ $V_{CE(sat)}$
High current gain, Low collector-emitter saturation voltage.

v ̈Ω Parameter	ϒ N Symbol	̈Ω Ö Rating	D Ч Unit
Collector to Base Voltage	V_{CBO}	-50	V
Collector to Emitter Voltage	V_{CEO}	-45	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-100	mA
Collector Power Dissipation	P_C	350	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

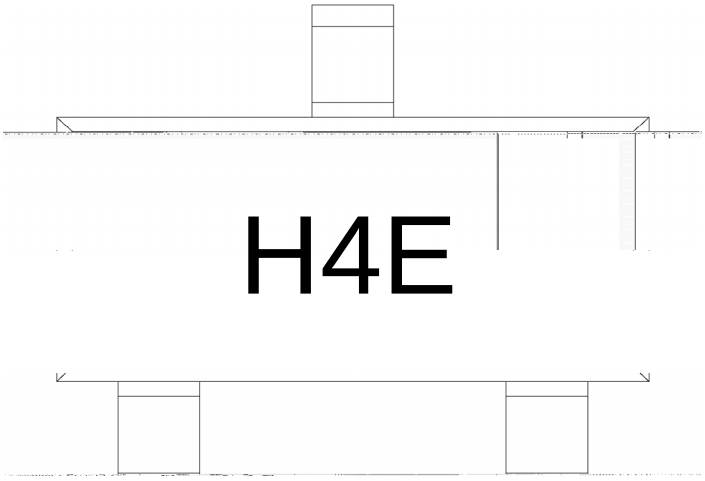
v ̈Ω Parameter	ϒ N Symbol	╜ ; ┤ ţ Test Conditions	ω ņ Ö Min	Ɛ ʒ Ö Typ	ω ᶻ Ö Max	D Ч Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=-10mA I_B=0	-45			V
Collector to Base Breakdown Voltage	V_{CBO}	I_CC I	E		O	

/ Package Dimensions





/ Marking Instructions



ب ˝ χ

K χ ѭ ҳ и Ґ

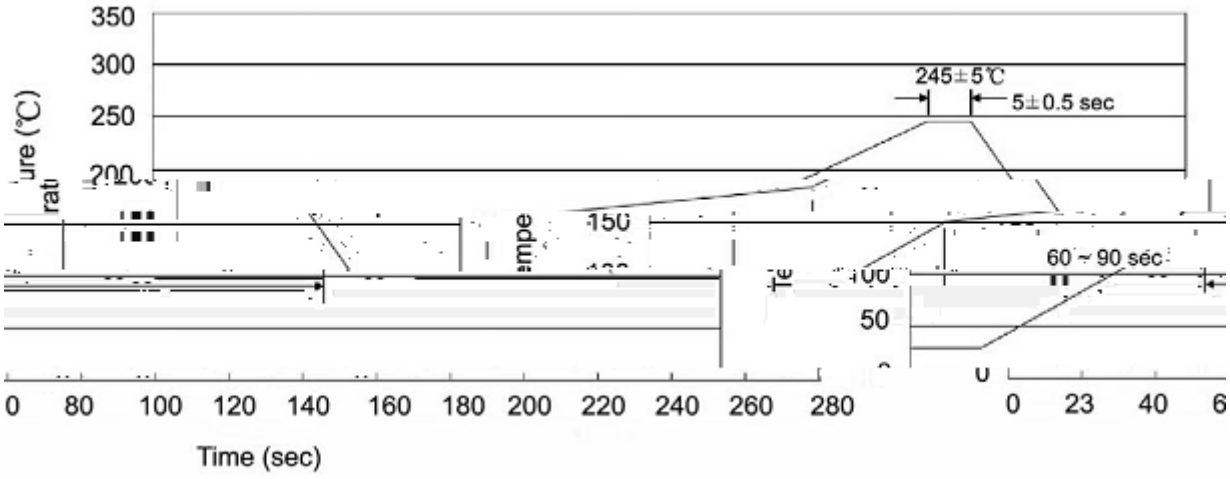
7H χ ѭ ҷ N Ґ

Note:

H: Company Code.

4E: Product Type Code

( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)



ب ˝ χ

1 Ĺ ♬ □ ỷ 25 Ḱ 150 ł ı `H ڑ 60 Ḱ 90sec;

2 Š Ө □ ỷ 245 ° 5 ł ı `H ڑ `Y ﾊ ㎞ 5 ° 0.5sec;

3 ì ˙ Ⅵ ˛ ɔ ﻉ ỷ ㎞ 2 Ḱ 10 ł /sec.

Note:

1.Preheating:25~150 ł , Time:60~90sec.

2.Peak Temp.:245 ° 5 ł , Duration:5 ° 0.5sec.

3. Cooling Speed: 2~10 ł /sec.

/ Resistance to Soldering Heat Test Conditions

□ ỷ χ 260±5 `H ڑ χ 10±1 sec. Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

ɔ ` ɣ Ł / REEL

Package Type	Units					Dimension		(unit mm^3)
	Units/Reel /	Reels/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Reel	Inner Box	Outer Box
SOT-23	3,000	10	30,000	6	180,000	7 ×8	180×120×180	390×385×205

/ Notices